

200mA 40V Low Leak(0.37mm)

Chip Information

| | |
|-------------------|-----------------|
| Chip Size | 0.37 x 0.37mm |
| Pad Size | 0.30 x 0.30mm |
| Chip Quantity | 80698 pcs/wafer |
| Scribe Line Width | 40um |
| Passivation | SIN |
| Wafer Size | 5 inch |
| Top Metallization | Al(For Wire) |

Chip Thickness/Back Metal : See below "Ordering Information"

MAXIMUM RATINGS

| Parameter | Symbol | Limit | Unit | Note |
|---|---------|-------------|------|-----------------------------|
| Repetitive Peak Reverse Voltage | VRRM | 40 | V | |
| Non-Repetitive Peak Reverse Voltage | VRSM | | V | |
| Maximum DC Blocking Voltage | VR | 40 | V | |
| Average Forward Rectified Current | IF(AV) | 200 | mA | |
| Peak Forward Surge Current | IFSM | 1 | A | 8.3ms Single Half Sine-Wave |
| Storage and Operating Temperature Range | Tj,TSTG | -65 to +125 | degC | |

ELECTRICAL CHARACTERISTICS

| Parameter | Symbol | Spec Limit | Probe Spec | Typical | Unit | Test Condition |
|----------------------------|--------|------------|------------|---------|------|--------------------|
| Maximum Forward Voltage | VF1 | 0.600 | 0.575 | 0.530 | V | IF=200mA Ta=25degC |
| | VF2 | 0.450 | 0.425 | 0.332 | V | IF=10mA Ta=25degC |
| | VF3 | | | | V | |
| | VF4 | | | | V | |
| | VF5 | | | | V | |
| Maximum DC Reverse Current | IR1 | 1 | 0.3 | 0.08 | uA | VR=10V Ta=25degC |
| | IR2 | 2 | 1 | 0.35 | uA | VR=40V Ta=25degC |
| | IR3 | | | | uA | |
| | IR4 | | | | uA | |
| Reverse Breakdown Voltage | BV | 40 | 44 | 52 | V | IR=10uA |
| Junction Capacitance | Cj | | | | pF | |
| Reverse Recovery Time | trr | | | | nS | |

Ordering Information

| Chip Type | Chip Thickness | Back Metal |
|-----------|----------------|------------------------|
| XHB06B | 140 +/- 20um | Ti-Ni-Ag(For Ag Epoxy) |
| XHB06C | 140 +/- 20um | Au(For Eutectic) |
| XHB06Y | 120 +/- 20um | Ti-Ni-Ag(For Ag Epoxy) |

Note:

Designed For RB520S-30,RB520S-40